Features

- High Density Cell Design for Low RDS(ON)
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

DUAL N-Channel MOSFET

Maximum Ratings

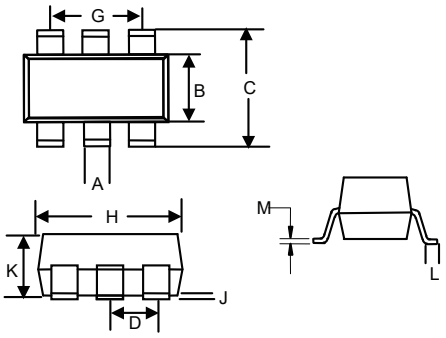
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 416°C/W Junction to Ambient(Note 2)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	500	mA
	T_A=100°C		316	
Pulsed Drain Current(Note 3)		I_{DM}	2	A
Total Power Dissipation(Note 4)		P_D	300	mW

Note:

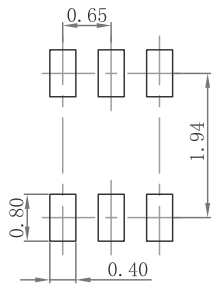
1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of RθJA is measured with the device mounted on the minimum recommend pad size, in the still air environment with TA =25℃.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

SOT-363

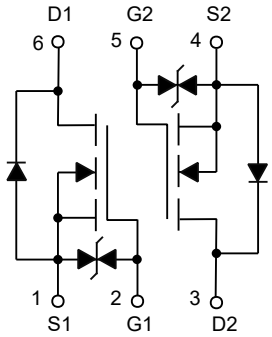


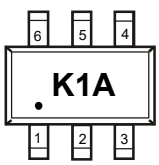
DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.006	0.014	0.15	0.35	
B	0.045	0.053	1.15	1.35	
C	0.079	0.096	2.00	2.45	
D	0.026		0.65		TYP.
G	0.047	0.055	1.20	1.40	
H	0.071	0.087	1.80	2.20	
J	-----	0.004	-----	0.10	
K	0.031	0.043	0.80	1.10	
L	0.010	0.018	0.26	0.46	
M	0.003	0.006	0.08	0.15	

Suggested Solder Pad Layout



Internal Structure and Marking Code





Dot Denotes Pin1

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250uA	30			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±10	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	0.7	1.1	1.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=300mA		424	750	mΩ
		V_{GS}=4.5V, I_D=200mA		596	960	
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=0.5A		579		mS
Gate Resistance	R_g	V_{GS}=0V, f=1MHz		86		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				0.5	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=250mA			1.2	V
Reverse Recovery Time	t_{rr}	I_F=0.5A, dI_F/dt=100A/μs		8.6		ns
Reverse Recovery Charge	Q_{rr}			1.6		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V,f=1MHz		13.9		pF
Output Capacitance	C_{oss}			6		
Reverse Transfer Capacitance	C_{rss}			1.8		
Total Gate Charge	Q_g	V_{DS}=15V,V_{GS}=10V,I_D=0.5A		0.8		nC
Gate-Source Charge	Q_{gs}			0.2		
Gate-Drain Charge	Q_{gd}			0.1		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=15V,V_{GS}=10V, I_D=0.5A,R_G=6Ω		2.2		ns
Turn-On Rise Time	t_r			2.9		
Turn-Off Delay Time	$t_{d(off)}$			7		
Turn-Off Fall Time	t_f			7.3		

Curve Characteristics

Fig.1 - Typical Output Characteristics

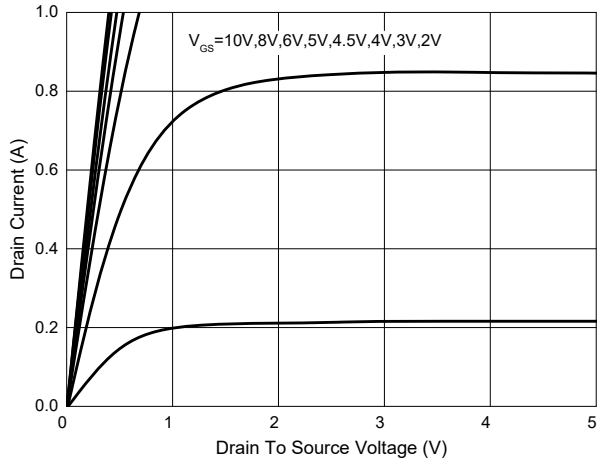


Fig.2 - Transfer Characteristic

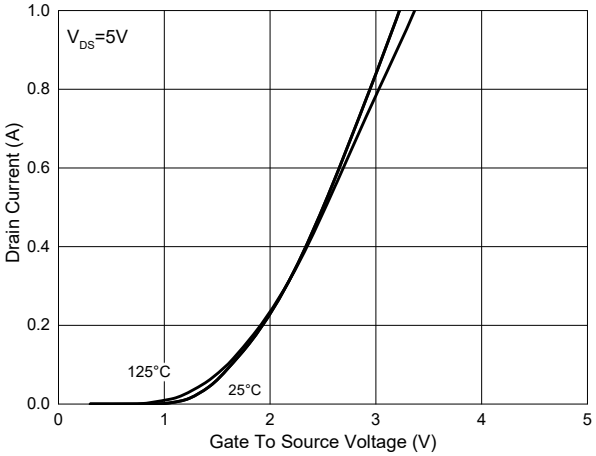


Fig.3 - $R_{DS(ON)}$ - V_{GS}

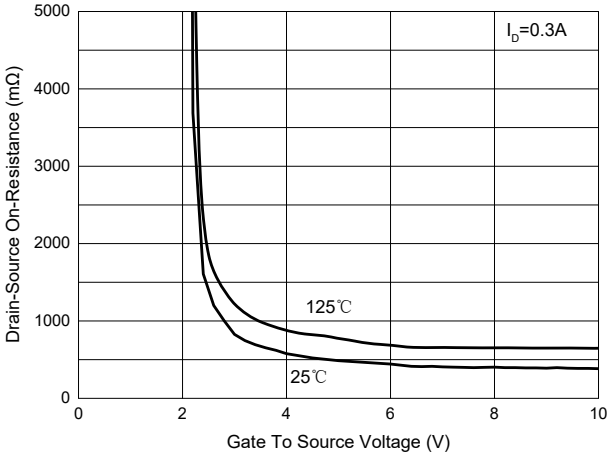


Fig.4 - $R_{DS(ON)}$ - I_D

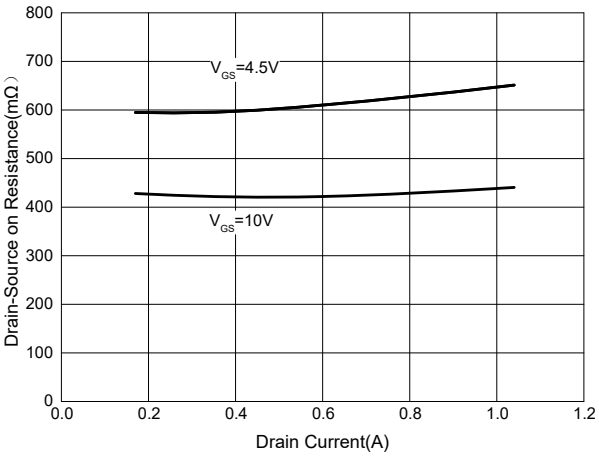


Fig.5 - Capacitance Characteristics

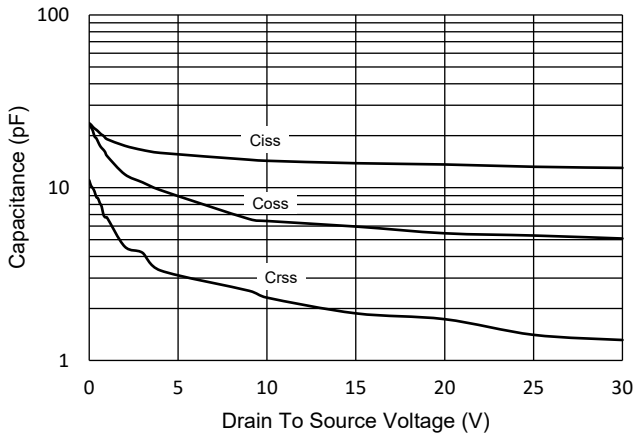
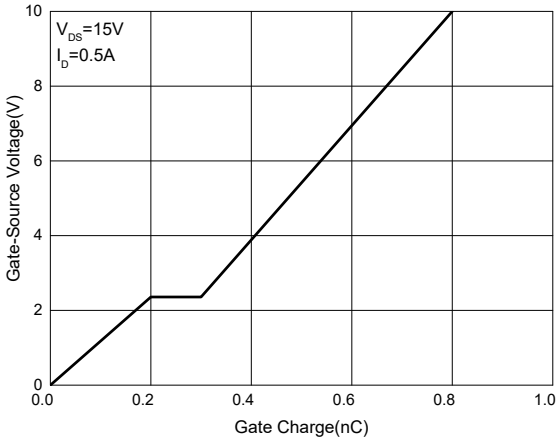


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

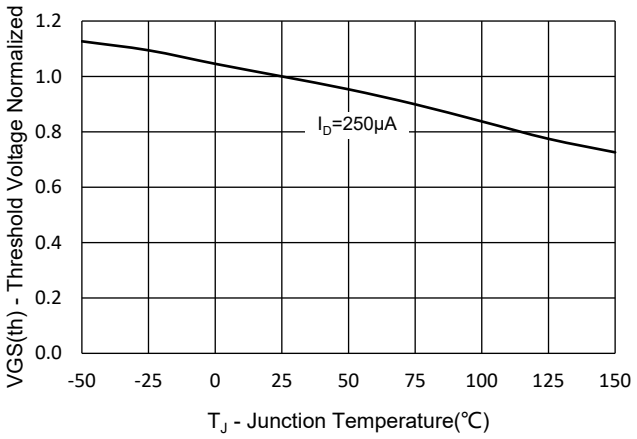


Fig.8 - Normalized On Resistance Characteristics

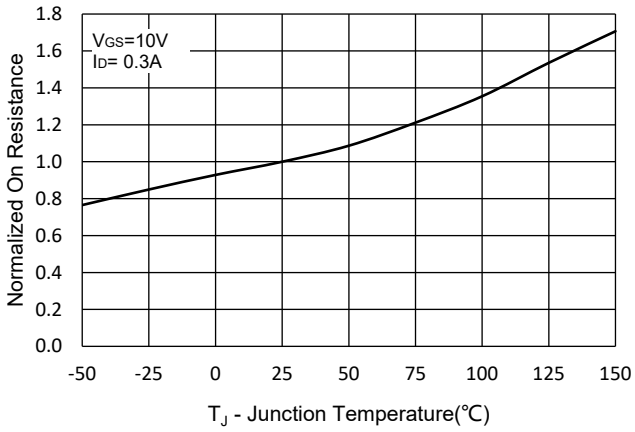


Fig.9 - I_S - V_{SD}

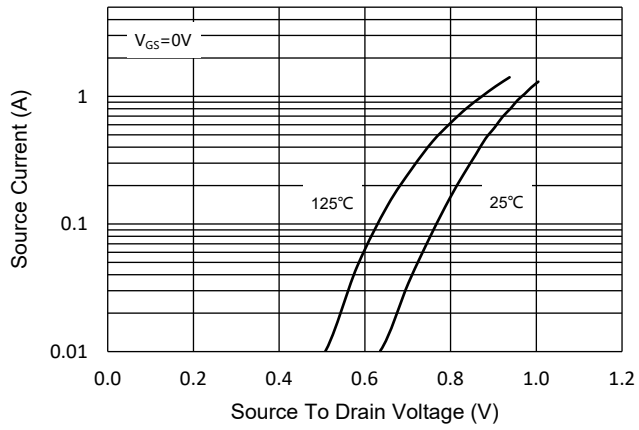


Fig.10 - Drain Current

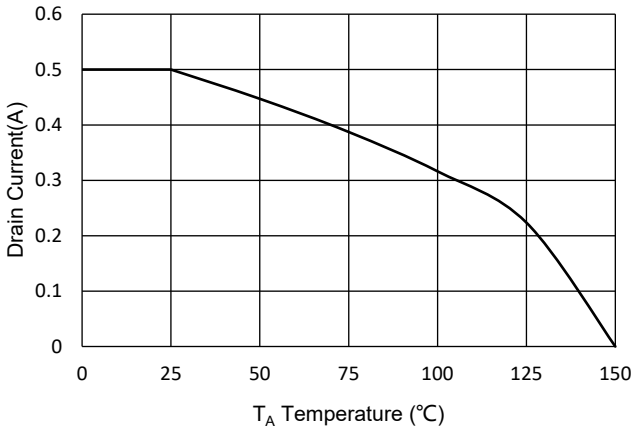
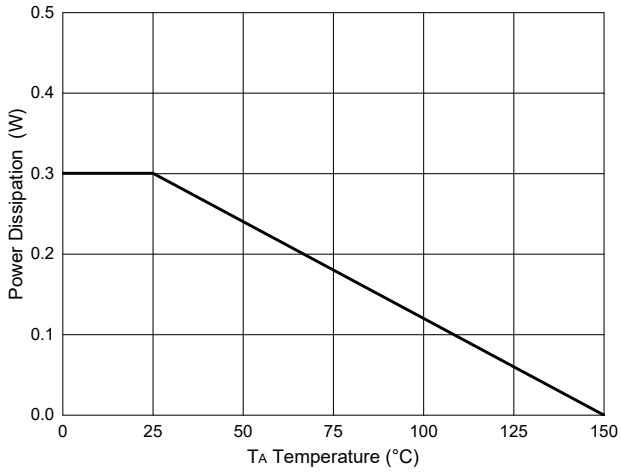


Fig.11 - PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

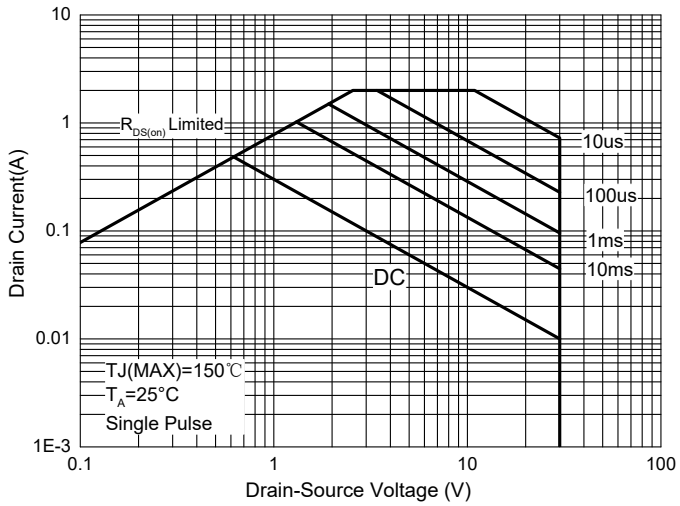
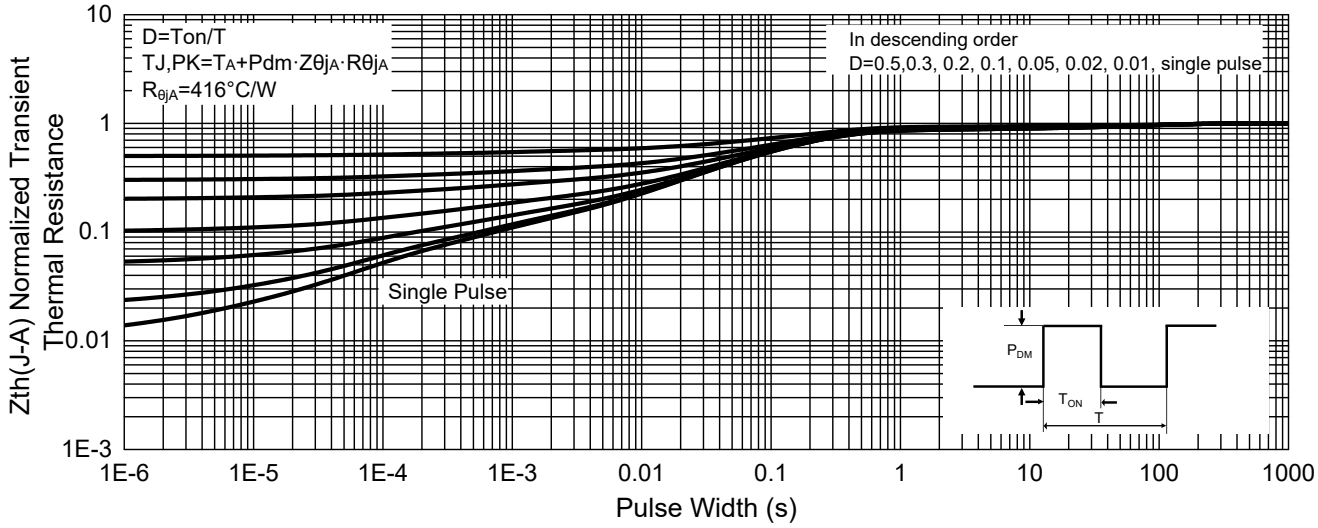


Fig. 13 -Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel
Part Number-TPQ2	Tape&Reel:3Kpcs/Reel

For packaging details, go to our website at https://www.mccsemi.com/pdf/ProductPackaging/SOT-363%20Package.pdf